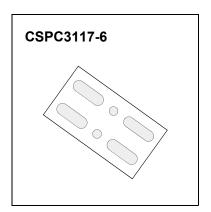


CSP Enhancement Mode Power MOSFET

6208SP Dual N-Channel MOSFET

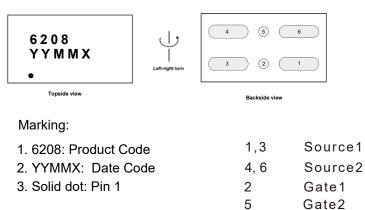
| V _{SSS} | R _{SS(on)} TYP | ls |
|------------------|-------------------------|-----|
| 12V | 2.0mΩ@4.5V | |
| | 2.1mΩ@3.8V | 12A |
| | 2.3mΩ@3.1V | |
| | 2.8mΩ@2.5V | |



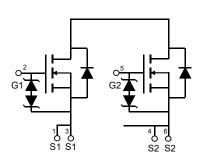
DESCRIPTION

The 6208SP uses advanced trench technology to provide excellent RSS(ON), low gate charge and operation with gate voltages as low as 2.5V while retaining a 8V VGS(MAX) rating. It is ESD protected. This device is suitable for use as a unidirectional or bi-directional load switch, facilitated by its common-drain configuration.

Marking and pin assignment



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---------------------------|--------------------------------|---------------------------------|------|
| Source to Source Voltage | V _{SSS} | 12 | V |
| Gate-Source Voltage | V _{GSS} | ±8 | V |
| Source Current(DC) | l _s ^① 12 | | А |
| Source Current (Pulsed) | I _{SP} ^① | 120 | А |
| Total Power Dissipation | PT ^① | P _T ^① 2.0 | |
| Channel Temperature | T _{ch} | 150 | °C |
| Storage Temperature Range | T _{STG} | -55 To 150 | °C |

MOSFET ELECTRICAL CHARACTERISTICS

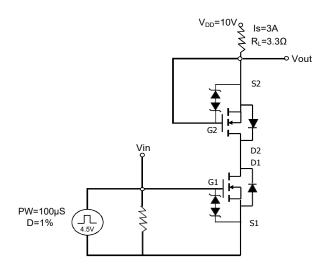
$T_a \text{=} 25 \ ^\circ \!\! C$ unless otherwise specified

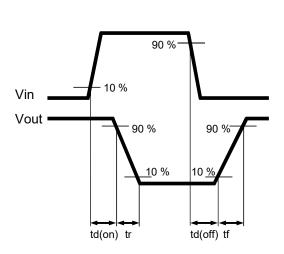
| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|---|---------------------|---|-----|------|-----|------|
| Static Parameters | | | - | • | | |
| Source to Source Breakdown Voltage | BV _{SSS} | I _S =1mA ,V _{GS} =0V | 12 | | | V |
| Zero-Gate Voltage Source Current | I _{SSS} | V _{SS} =10V,V _{GS} =0V | | | 1.0 | μA |
| Gate to Source Leakage Current | I _{GSS} | V _{SS} =0V,V _{GS} = ±8V | | | ±10 | μA |
| Gate to Source Threshold Voltage | V _{GS(th)} | V _{SS} =V _{GS} , I _S =1.41mA | 0.4 | 0.93 | 1.2 | V |
| Source to Source On-state Resistance | R _{SS(on)} | V _{GS} =4.5V,I _S =3A | 1.2 | 2.0 | 2.8 | mΩ |
| | | V _{GS} =3.8V,I _S =3A | 1.3 | 2.1 | 3.0 | mΩ |
| | | V _{GS} =3.1V,I _S =3A | 1.4 | 2.3 | 3.3 | mΩ |
| | | V _{GS} =2.5V,I _S =3A | 1.7 | 2.8 | 4.0 | mΩ |
| Input Capacitance | Ciss | Ciss Coss V _{SS} =10V, V _{GS} =0V,f=1kHz Crss | | 4262 | | pF |
| Output Capacitance | Coss | | | 897 | | pF |
| Reverse Transfer Capacitance | Crss | | | 696 | | pF |
| Turn-on Delay Time | t _{d(on)} | | | 1.5 | | μS |
| Turn-on Rise Time | tr | | | 4.5 | | μS |
| Turn-off Delay Time | t _{d(off)} | | | 6.8 | | μS |
| Turn-off Fall Time | t _f | | | 11.4 | | μS |
| Total Gate Charge | Qg | V _{DD} =10V,I _S =6A,V _{GS} =4.5V | | 49.2 | | nC |
| Gate1-source1 charge | Q _{g1s1} | | | 10.8 | | nC |
| Gate1-source2 charge | Q _{g1s2} | | | 25.2 | | nC |
| Diode Forward Voltage | V _{F(S-S)} | V _{GS} =0V,I _S =3A | | | 1.0 | V |

Notes: 1.Mounted on FR4 board (25.4mm×25.4mm×t1.0mm) using the minimum recommended pad size (36um Copper).

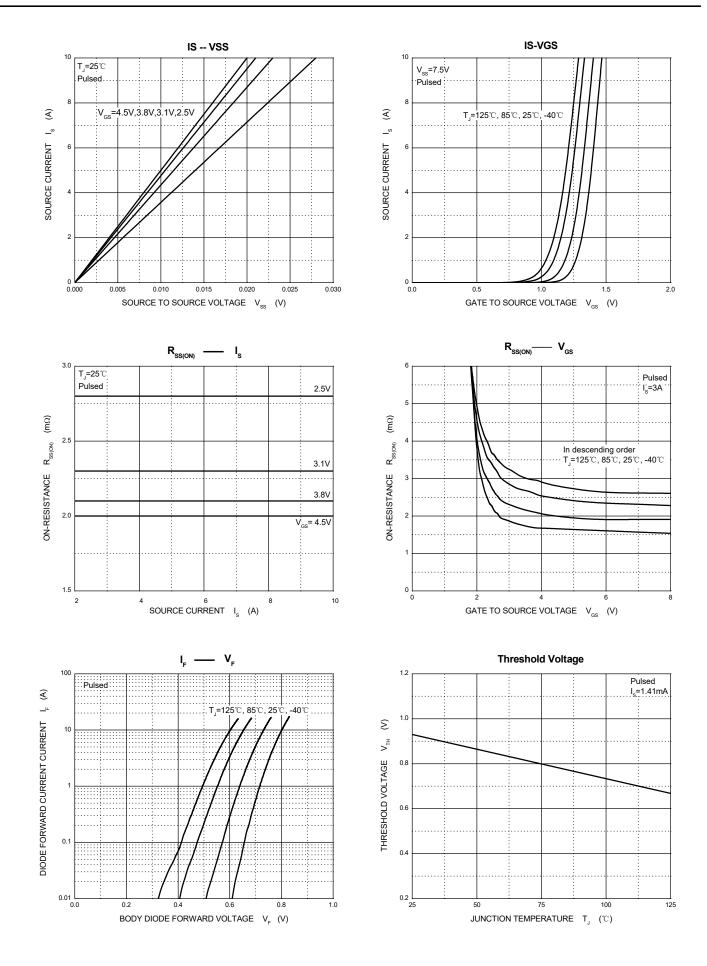
2.t = 10 ms , Duty Cycle = 1 %.

 $\ensuremath{\texttt{3.When}}\xspace$ FET1 is measured,G2 and S2 are short-circuited.



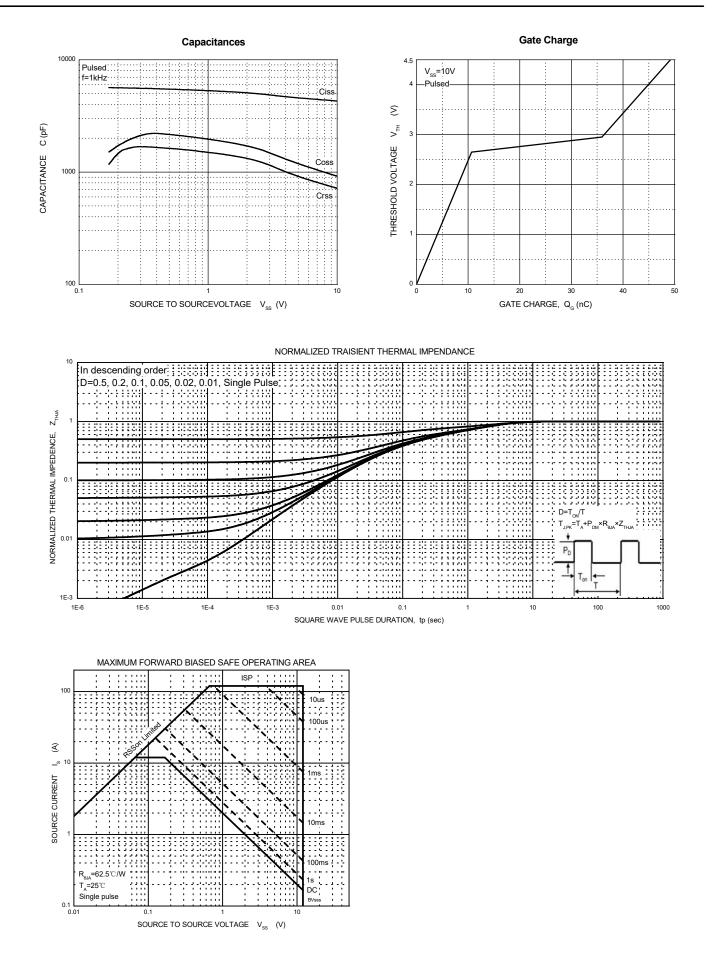


Typical Characteristics



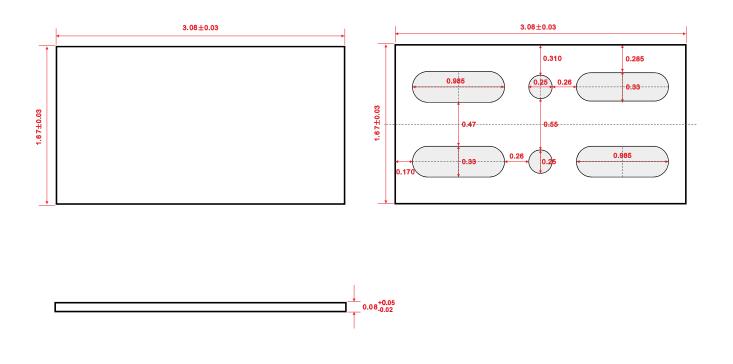
3

Typical Characteristics

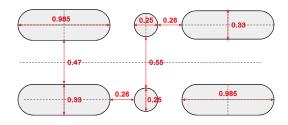


4

CSPC3117-6 Package Outline Dimensions(Unit:mm)



CSPC3117-6 Suggested Pad Layout (Unit:mm)



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.050mm.

3. The pad layout is for reference purposes only.

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